

Notic of References CitedApplication/Control No:
09/588,008Applicant(s)/Patent Under
Reexamination
YANG ET AL.Examiner
Vikki H TrinhArt Unit
2814

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name		Classification
	A	US-6489199	12-2002	Li et al.		438/253
	B	US-				
	C	US-				
	D	US-				
	E	US-				
	F	US-				
	G	US-				
	H	US-				
	I	US-				
	J	US-				
	K	US-				
	L	US-				
	M	US-				

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Yamagishi et al., Stacked Capacitor DRAM process using photo-CVD Ta?sub 2/O/sub, Electron Devices, IEEE Transaction on, Volume 35 Issue: 12, Dec 1988, p. 2439.
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.